

CORRECTION

## Correction to: Generation and Auto-Revealing of Dislocations in Si During Macropore Etching

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### Correction to:

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On page 5116, last paragraph in the XRD Data section, there is an error. The corrected sentence is as follows:

This leads to a temperature gradient greater than  $10^3$ °C/cm and a lattice deformation on the order of  $10^{-5}$ .

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